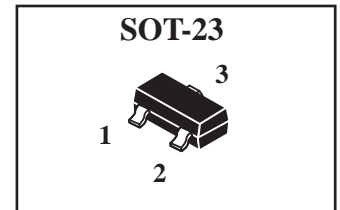
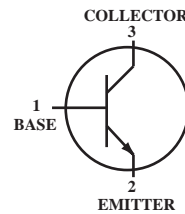


### High-Voltage NPN Transistor Surface Mount

 Lead(Pb)-Free



### Maximum Ratings

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	400	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	450	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current-Continuous	I <sub>C</sub>	300	mAdc

### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Total Device Dissipation FR-5 Board <sup>(1)</sup> T <sub>A</sub> =25 °C	P <sub>D</sub>	225	mW
Derate above 25 °C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	556	°C/W
Total Device Dissipation Alumina Substrate, <sup>(2)</sup> T <sub>A</sub> =25 °C	P <sub>D</sub>	350	mW
Derate above 25 °C		2.8	mW/°C
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	357	°C/W
Junction and Storage, Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

### Device Marking

MMBTA44=3D

### Electrical Characteristics (T<sub>A</sub>=25 °C Unless Otherwise noted)

Characteristics	Symbol	Min	Max	Unit
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### Off Characteristics

Collector-Emitter Breakdown Voltage <sup>(3)</sup> (I <sub>C</sub> =1.0mAdc, I <sub>B</sub> =0)	V <sub>(BR)CEO</sub>	400	-	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> =100 uAdc, I <sub>E</sub> =0)	V <sub>(BR)CBO</sub>	450	-	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> =10 uAdc, I <sub>C</sub> =0)	V <sub>(BR)EBO</sub>	6.0	-	Vdc
Base Cutoff Current (V <sub>CB</sub> =400 Vdc, I <sub>E</sub> =0)	I <sub>CBO</sub>	-	100	nAdc
Emitter Cutoff Current V <sub>EB</sub> =4V, I <sub>C</sub> =0	I <sub>EBO</sub>	-	100	nAdc

1.FR-5=1.0 x 0.75 x 0.062 in.

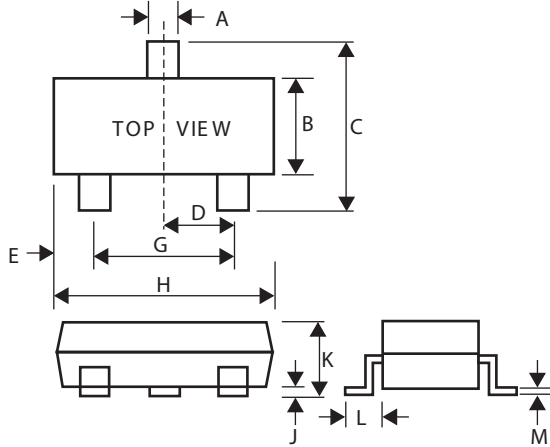
2.Alumina=0.4 x 0.3 x 0.024 in. 99.5% alumina.

3.Pulse Test:Pulse Width ≤300 μs, Duty Cycle ≤2.0%.

**Electrical Characteristics** ( $T_A=25\text{ }^\circ\text{C}$  unless otherwise noted) (Continued)

Characteristics	Symbol	Min	Max	Unit
<b>On Characteristics</b>				
DC Current Gain ( $I_C=1.0\text{ mA}$ , $V_{CE}=10\text{ Vdc}$ )	$H_{FE(1)}$	40	-	-
( $I_C=10\text{ mA}$ , $V_{CE}=10\text{ Vdc}$ )	$H_{FE(2)}$	50	2.00	-
( $I_C=50\text{ mA}$ , $V_{CE}=10\text{ Vdc}$ )	$H_{FE(3)}$	45	-	-
( $I_C=100\text{ mA}$ , $V_{CE}=10\text{ Vdc}$ )	$H_{FE(4)}$	20	-	-
Collector-Emitter Saturation Voltage <sup>(3)</sup> ( $I_C=1.0\text{ mA}$ , $I_B=0.1\text{ mA}$ )	$V_{CE(sat)}$	-	0.40	Vdc
( $I_C=10\text{ mA}$ , $I_B=1.0\text{ mA}$ )			0.50	
( $I_C=50\text{ mA}$ , $I_B=5.0\text{ mA}$ )			0.75	
Base-Emitter Saturation Voltage <sup>(3)</sup> ( $I_C=10\text{ mA}$ , $I_B=1.0\text{ mA}$ )	$V_{BE(sat)}$	-	0.75	Vdc
Current-Gain-Bandwidth Product ( $I_C=10\text{ mA}$ , $V_{CE}=10\text{ Vdc}$ , $f=10\text{ MHz}$ )	$f_T$	20	-	MHz

## SOT-23 Package Outline Dimension



SOT-23		
Dim	Min	Max
A	0.35	0.51
B	1.19	1.40
C	2.10	3.00
D	0.85	1.05
E	0.46	1.00
G	1.70	2.10
H	2.70	3.10
J	0.01	0.13
K	0.89	1.10
L	0.30	0.61
M	0.076	0.25